

An Electromagnetic Emission Model for Integrated Circuits

Peter Kralicek

FhG-IZM Paderborn/Berlin • University of Paderborn

Kralicek@ieee.org

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Overview

- Motivation/Introduction
- General Modeling
- Proposed Emission Model
- Modeling example
- Summary



Motivation: **Problems and their solutions**

System/PCB analysis:

- IC typically modeled by equivalent circuits → no direct contributions to emitted field
 - Not sufficient for today's high clock rates and complex packaging
 - Complete analysis of IC/package **and** PCB/system not possible:
 - high complexity
 - scale level differences
- ⇒ only practicable for small substructures

Development of macro-models representing essential properties



Modeling: Requirements

Requirements for an emission model:

- Good approximation of emitted fields (near- and far field)
- Low number of model parameters
- Parameter determination via measurement and simulation
- Simple integration into existing commercial tools for system/PCB analysis
- Considering different operation modes and connected circuitry



Modeling: **Different approaches**

Some possibilities of modeling EM-fields:

- Equivalence principle (known field values around IC)
- Superposition of plane waves (plane-wave spectrum)
- Equivalent radiating structures:
 - simple antennas: dipoles, loops (constant current distribution)
 - patch antennas
 - antennas with non-constant current distribution
- Multipole Expansion of electromagnetic field



Modeling: **Multipole Expansion I**

Solution of vector wave equation in spherical coordinates:

$$(\Delta + \mathbf{k}^2) \vec{\mathbf{C}} = 0 \quad \vec{\mathbf{C}} \in \{ \vec{\mathbf{E}}, \vec{\mathbf{B}}, \vec{\Pi}^{e,m} \}$$

leads to field expansion in orthogonal functions:

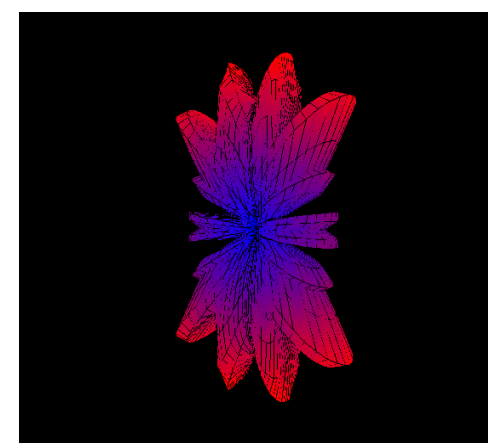
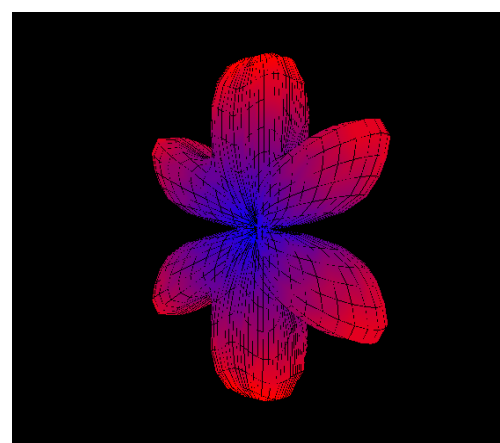
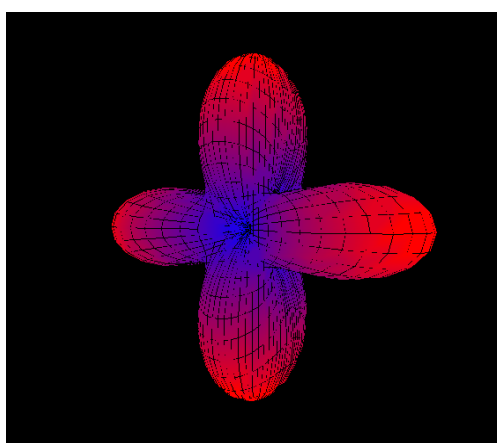
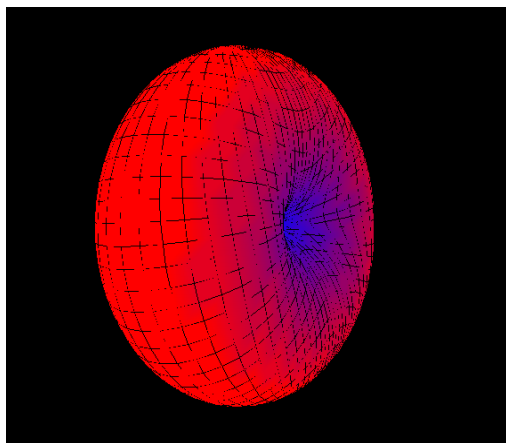
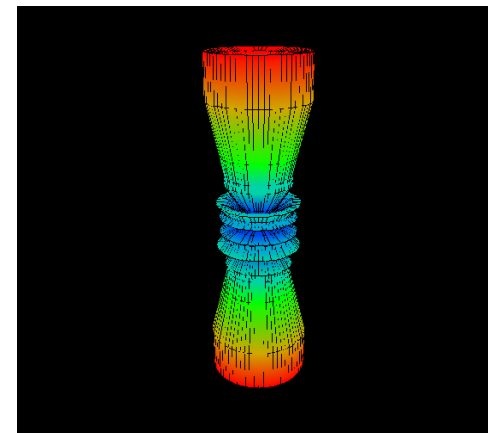
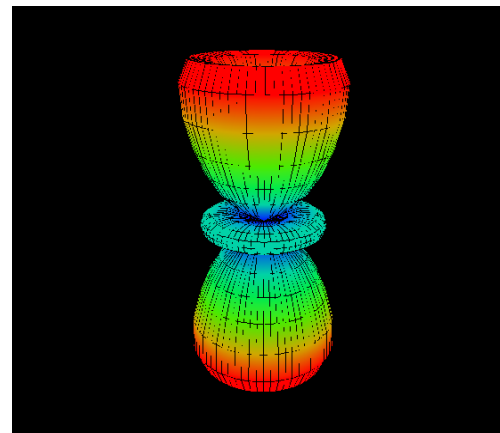
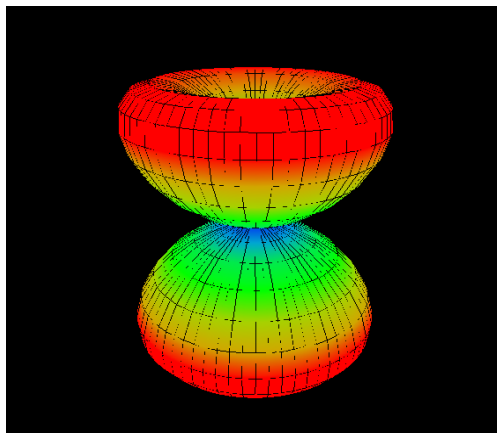
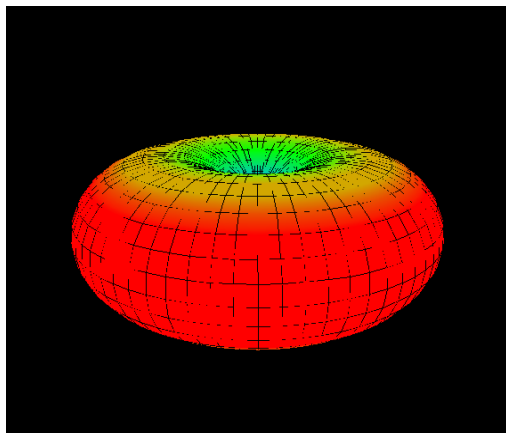
$$\left. \begin{matrix} \vec{\Pi}_e \\ \vec{\Pi}_m \end{matrix} \right\} = \frac{j}{k} \sum_{n=1}^{\infty} r h_n(kr) \sum_{m=0}^n P_n^m(\cos \vartheta) \left[\left\{ \begin{matrix} \mathbf{A}_{n,m} \\ \mathbf{C}_{n,m} / \mathbf{Z}_0 \end{matrix} \right\} \cos(m\varphi) + \left\{ \begin{matrix} \mathbf{B}_{n,m} \\ \mathbf{D}_{n,m} / \mathbf{Z}_0 \end{matrix} \right\} \sin(m\varphi) \right] \cdot \vec{\mathbf{e}}_r$$

$$\vec{\mathbf{E}} = \nabla \times \nabla \times \vec{\Pi}_e - j\omega\mu \nabla \times \vec{\Pi}_m \quad \vec{\mathbf{H}} = \nabla \times \nabla \times \vec{\Pi}_m + j\omega\varepsilon \nabla \times \vec{\Pi}_e$$

⇒ Expansion of el. and magnetic field in space outside sources



Modeling: **Multipole Expansion II**



Dipole

Quadrupole

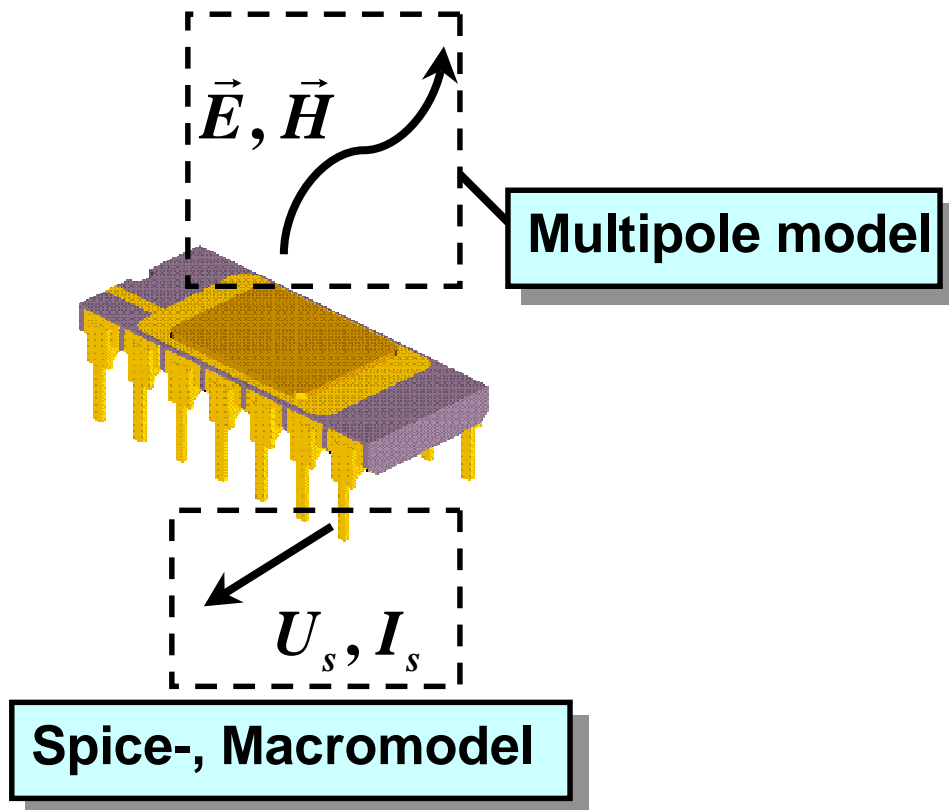
Octupole

Hexapole



Proposed Model: **Simple Emission Model**

Simple Emission Model (SEM)



- + Valid in near- and farfield
- + physical model
- + parameter determination via measurement or simulation
- no consideration of external circuitry

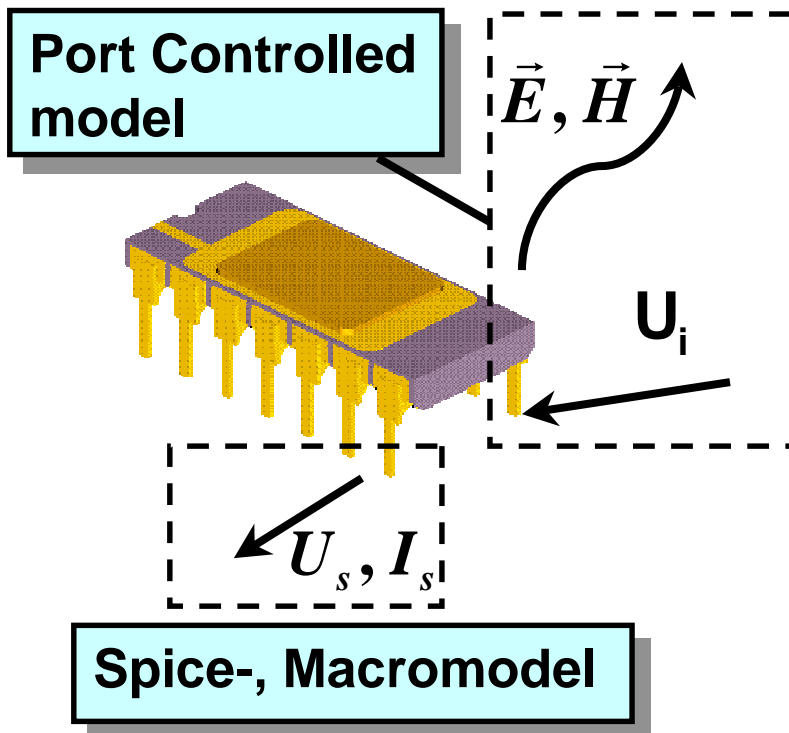
Model parameters:

- Multipole coefficients
- Optionally different operation modes



Proposed Model: **Controlled Emission Model**

Voltage Controlled Emission Model (VCEM)



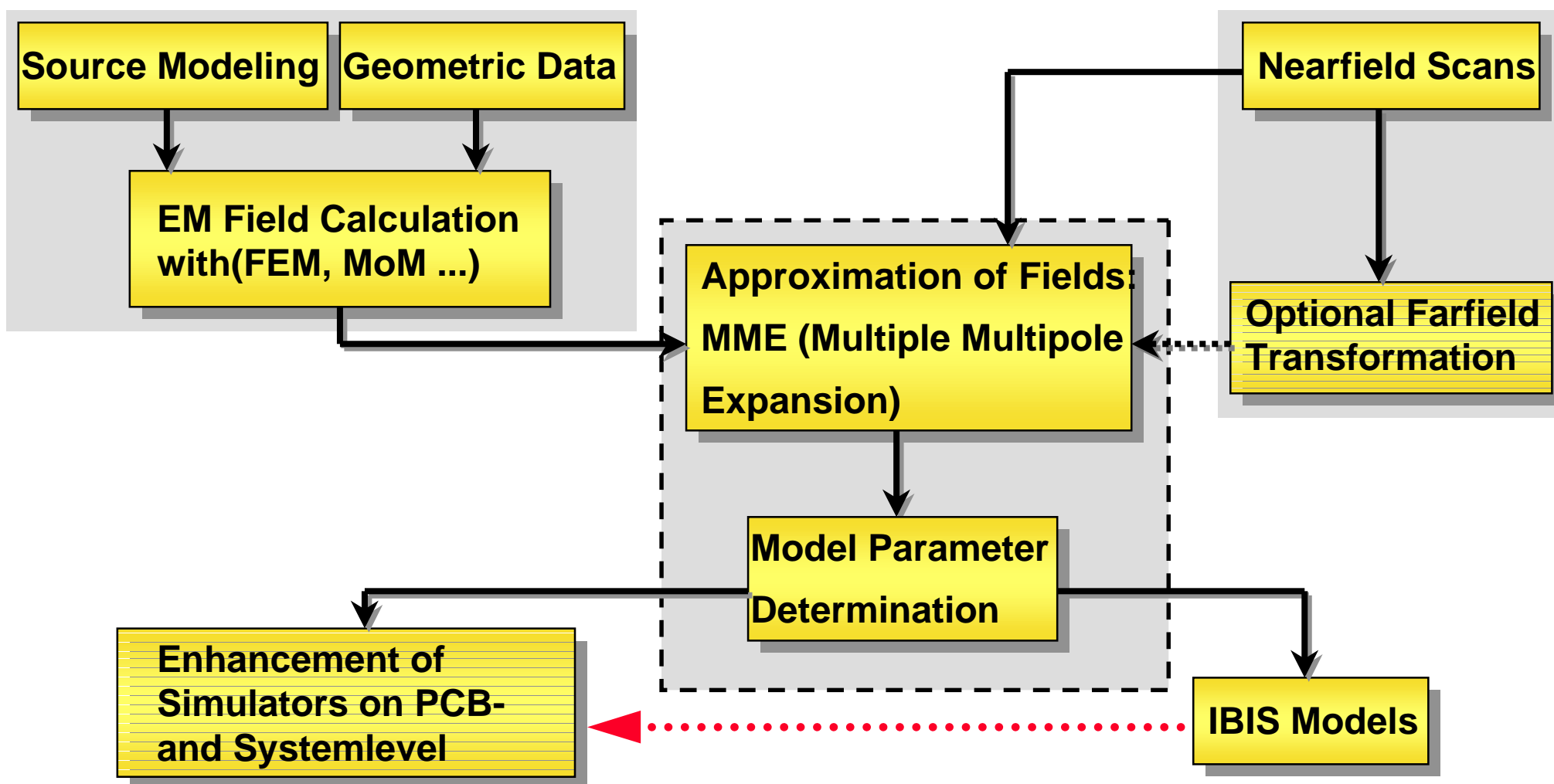
Electromagnetic equivalent model:

$$\overline{\overline{T'}} \cdot (\overline{u} - \overline{u}_0) + \overline{m}_0 = \overline{m}$$

- voltages at IC ports control modal emissions
- + consideration of external circuitry
→ parasitics effects (unintentional signals)



Proposed Model: **Modeling Workflow**




Proposed Model: **Integration into High-Level Tools**

- Use of models with weak coupling in fieldsolver COMORAN
- Calculation of current and radiated fields considering the IC emissions
- only minimal increase in calculation time (MoM matrix dim. constant)

⇒ Linear system of equations to determine unknown currents:

$$\underline{\mathbf{A}} \cdot \vec{\mathbf{x}} = \vec{\mathbf{b}}$$

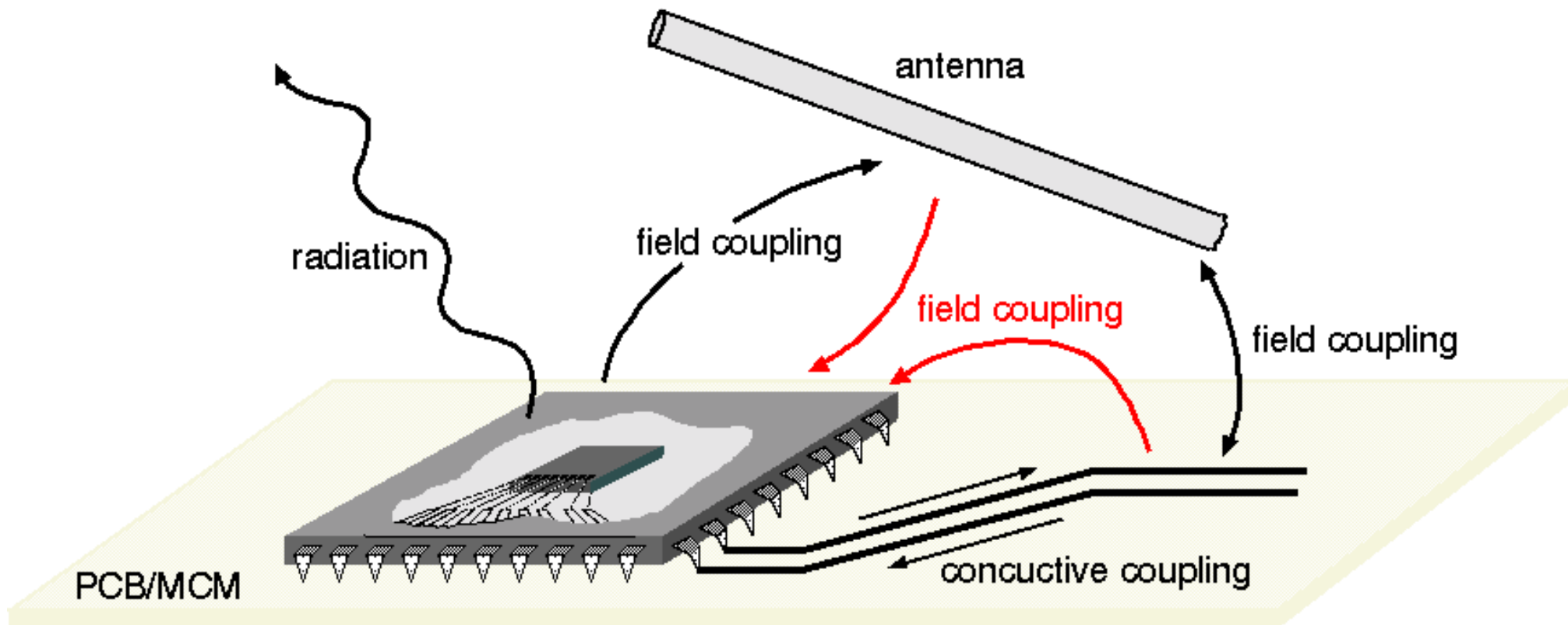
$\vec{\mathbf{E}}_{\text{Multipol}}$



Superposition of right side ***b*** by field contribution of multipoles



Proposed Model: **Coupling mechanisms**

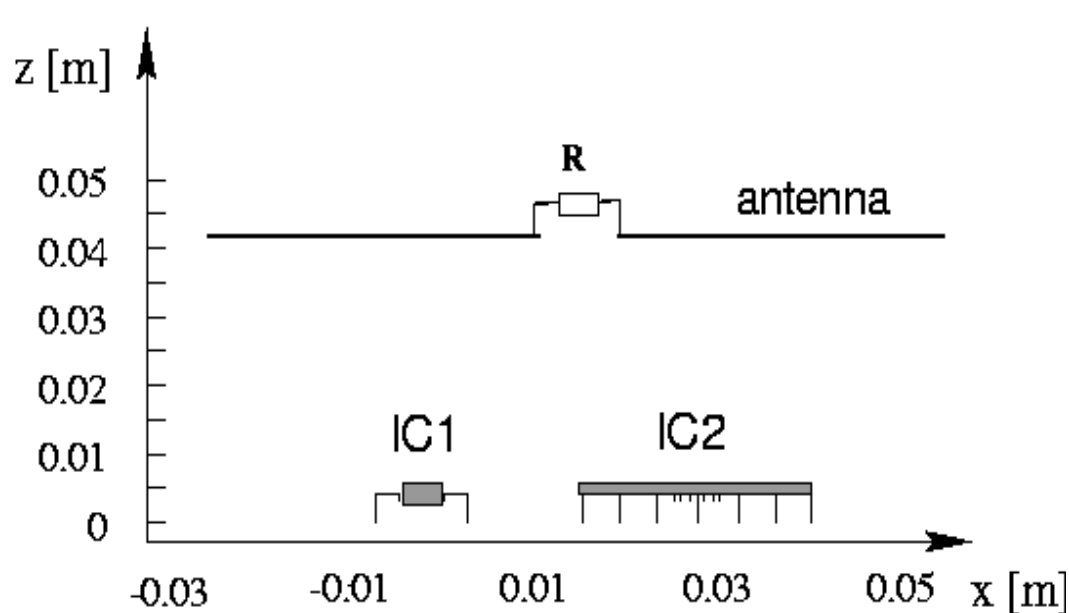


Coupling mechanisms covered by proposed models

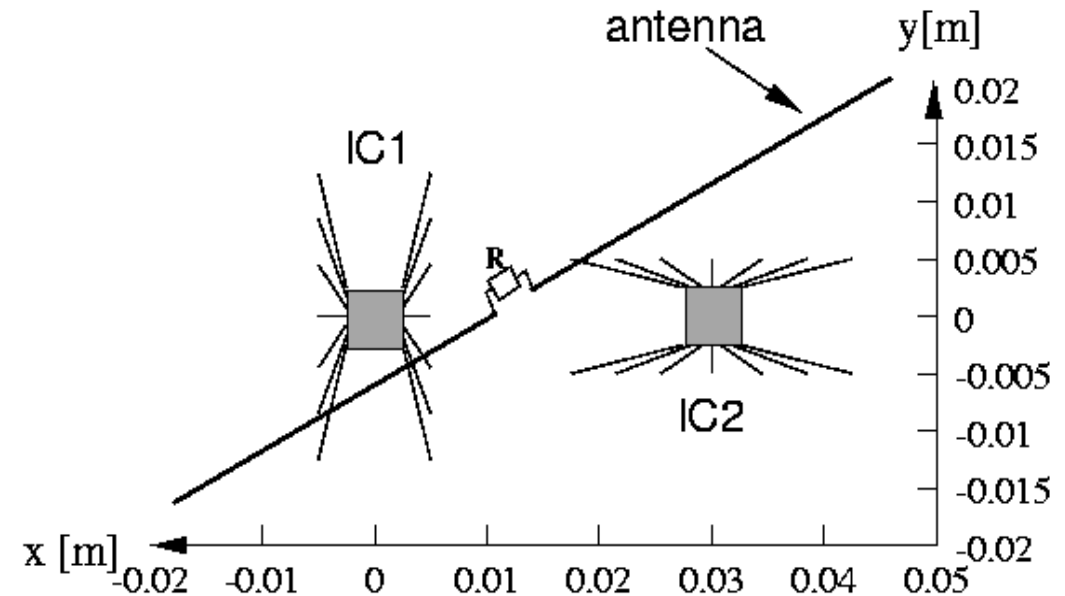


Example: **Complex Configuration**

Two IC with an antenna structure in the near-field



Side view of configuration

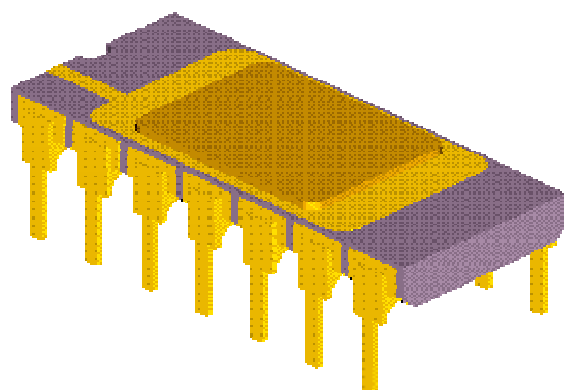


Top view of configuration

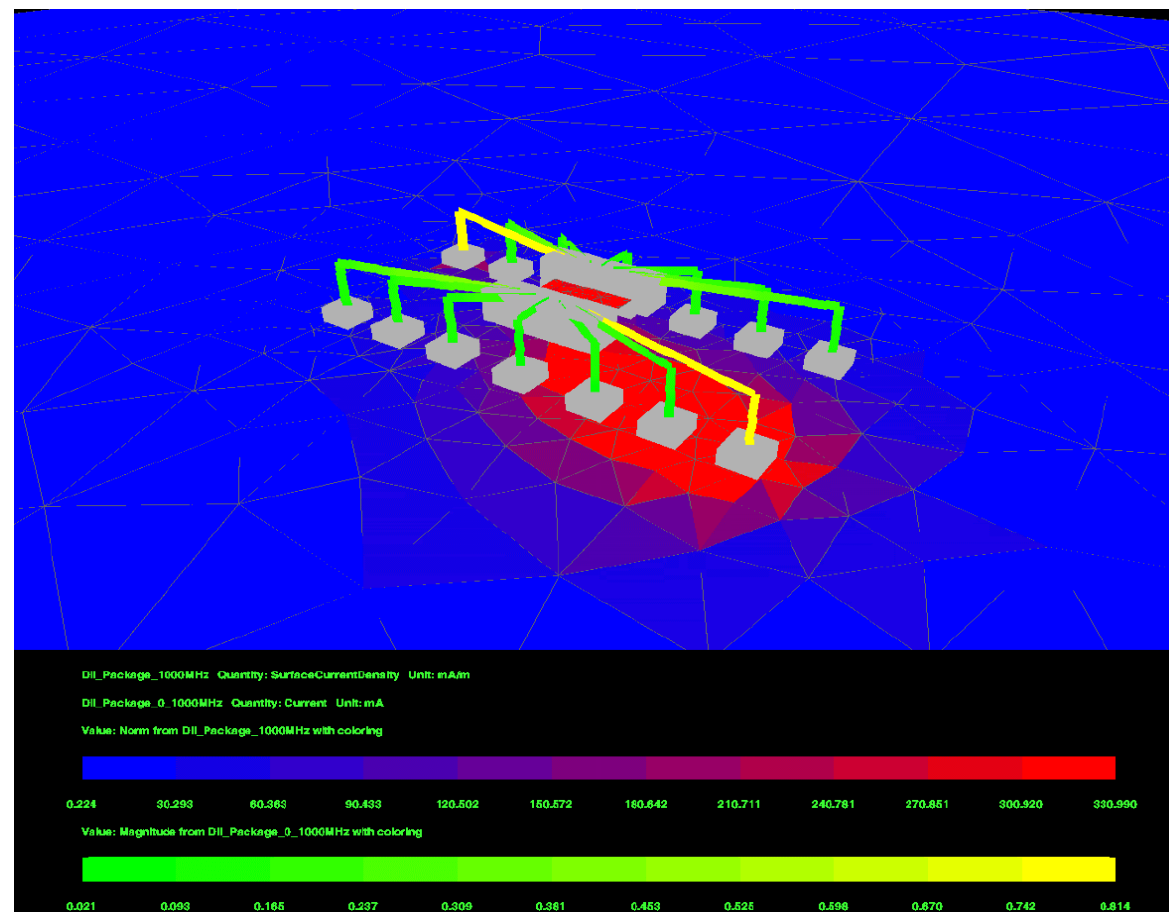
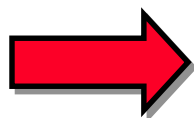
→ Image theory used for simplification, Simple Emission Model used



Example: **Complex Configuration**



IC/package

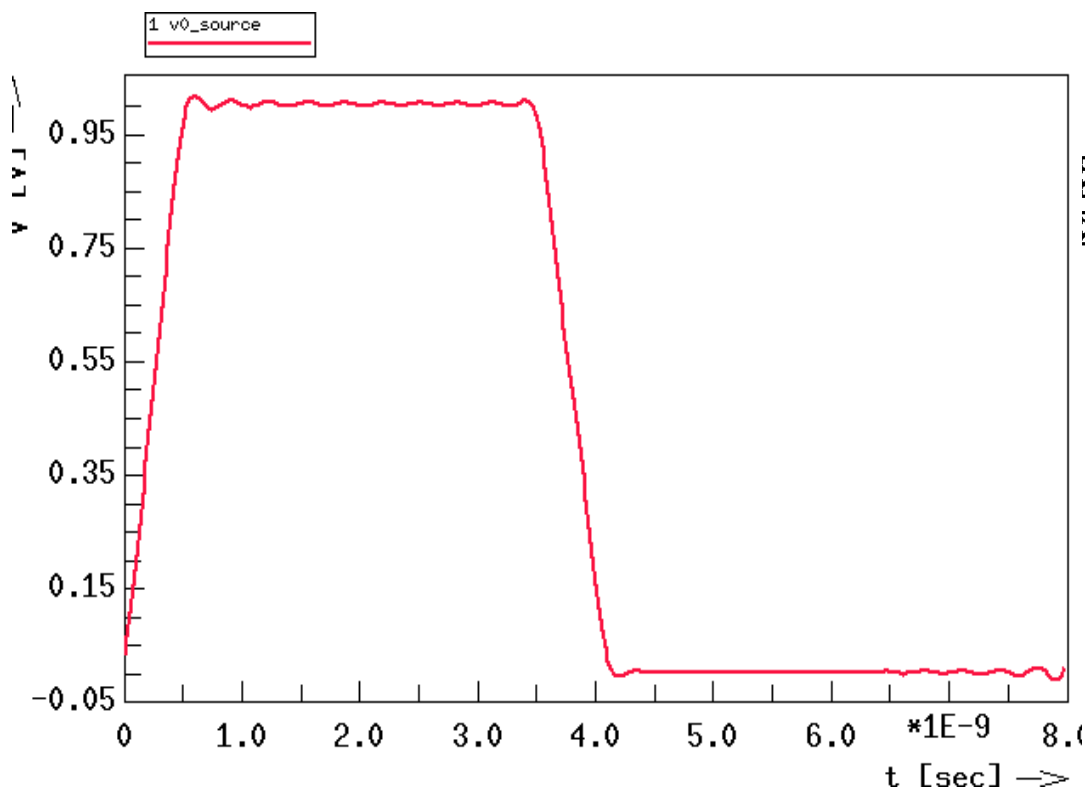


Current distribution at $f=2\text{GHz}$

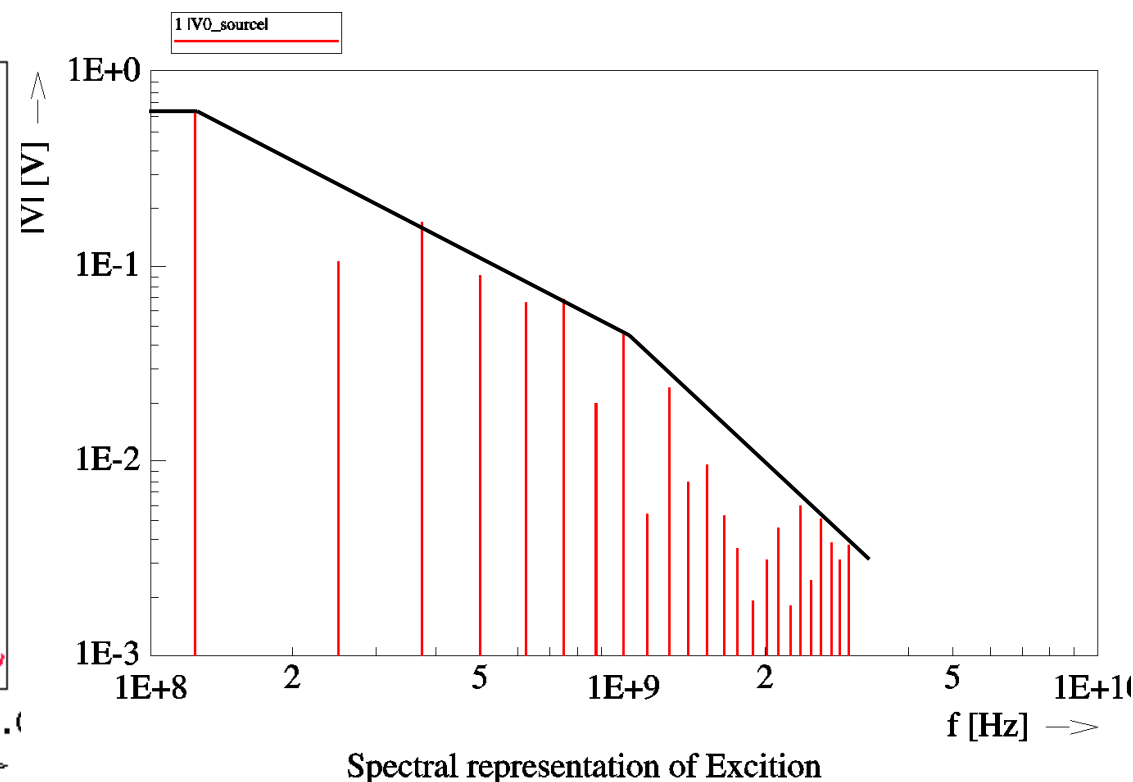
→ “*Simple*” geometric package model used to allow full-wave reference calculation of complete configuration



Example: **Excitation**



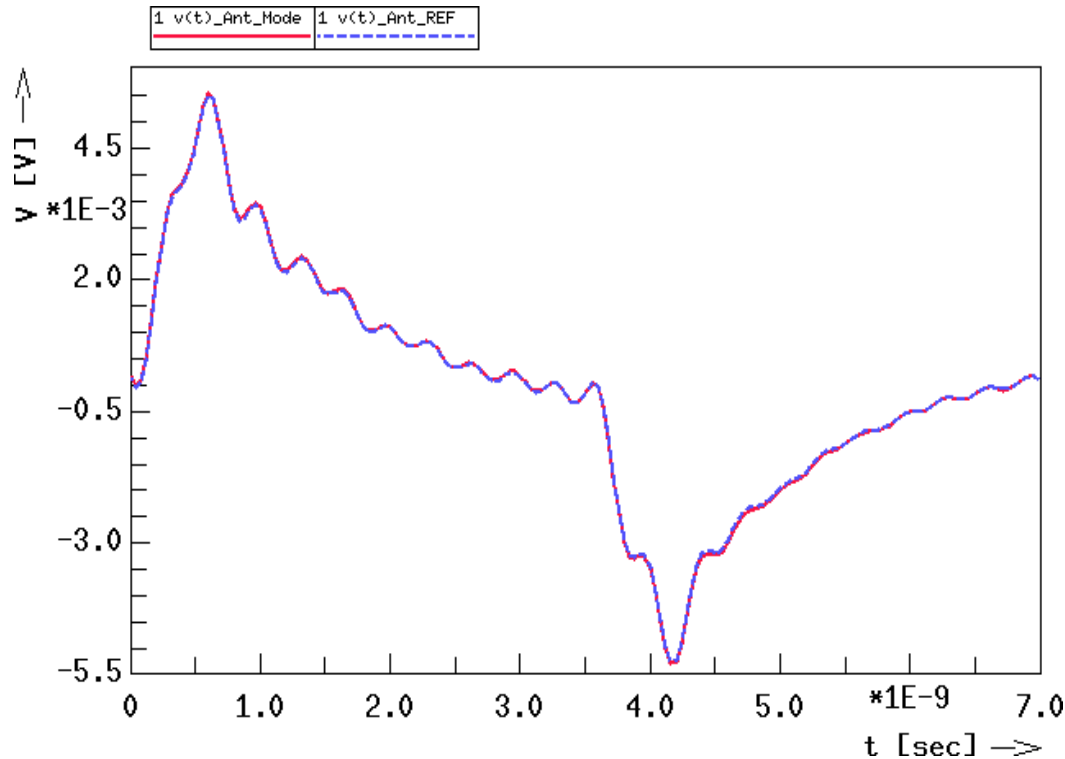
Excitation signal



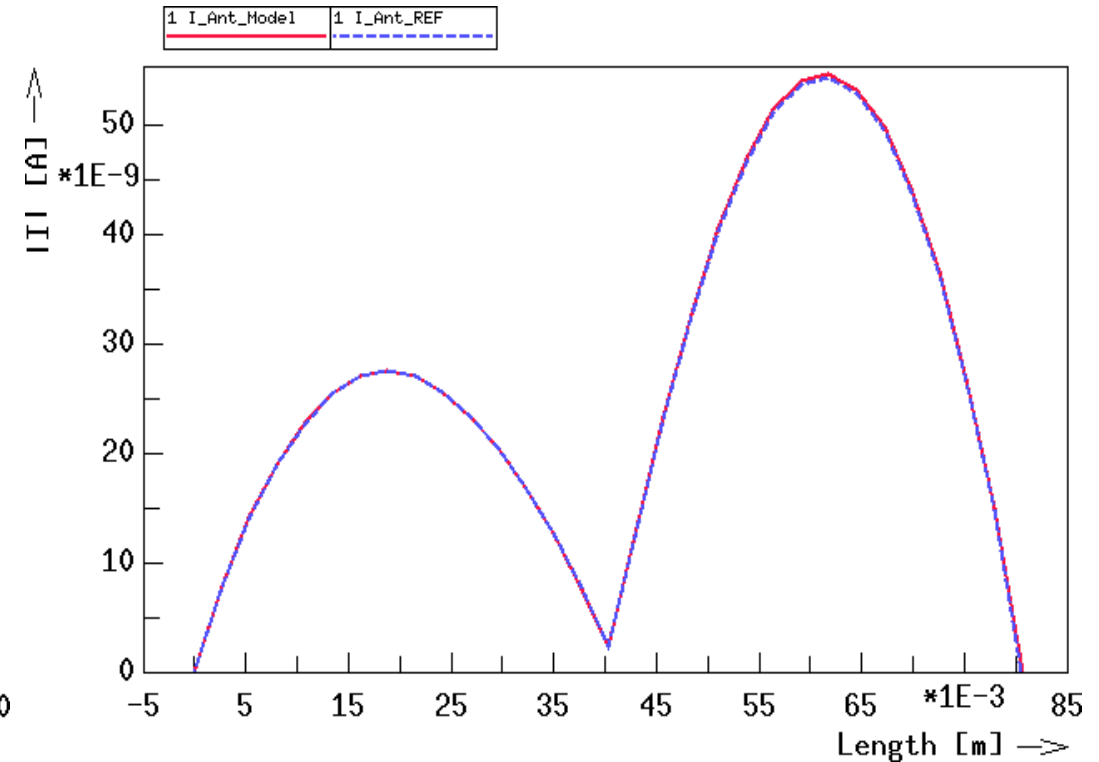
Respective spectrum (up to 3GHz)



Example: Nearfield-Effects



Time domain voltage at
antenna resistor

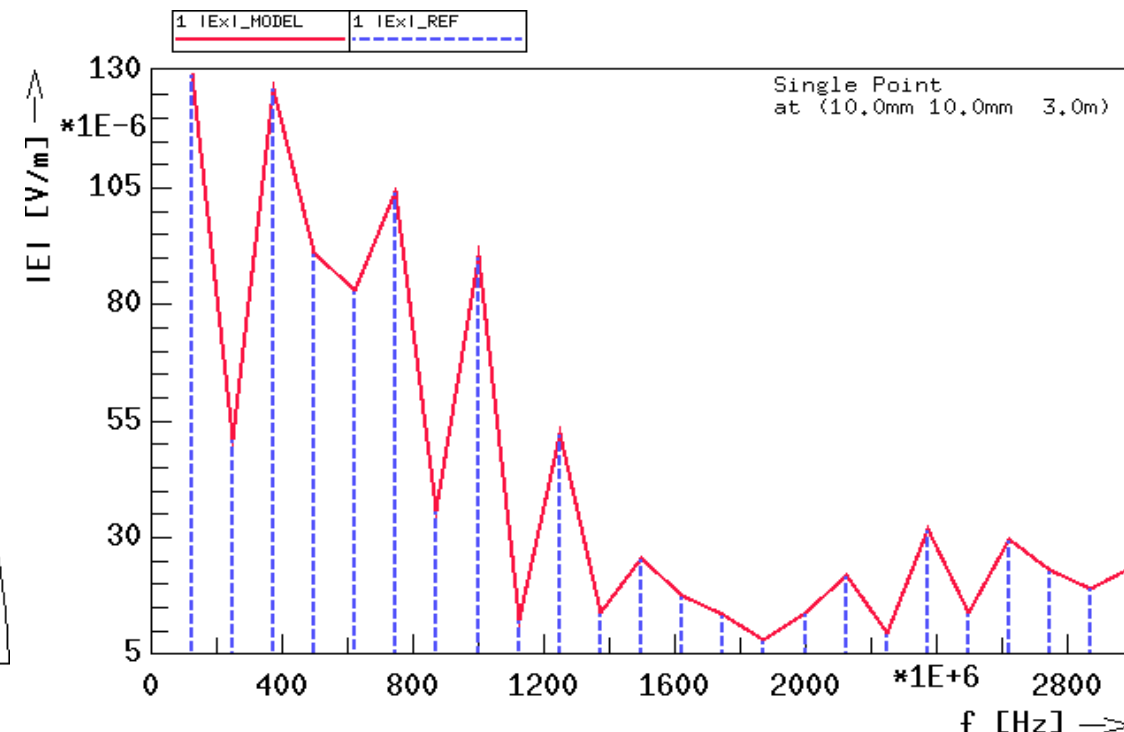
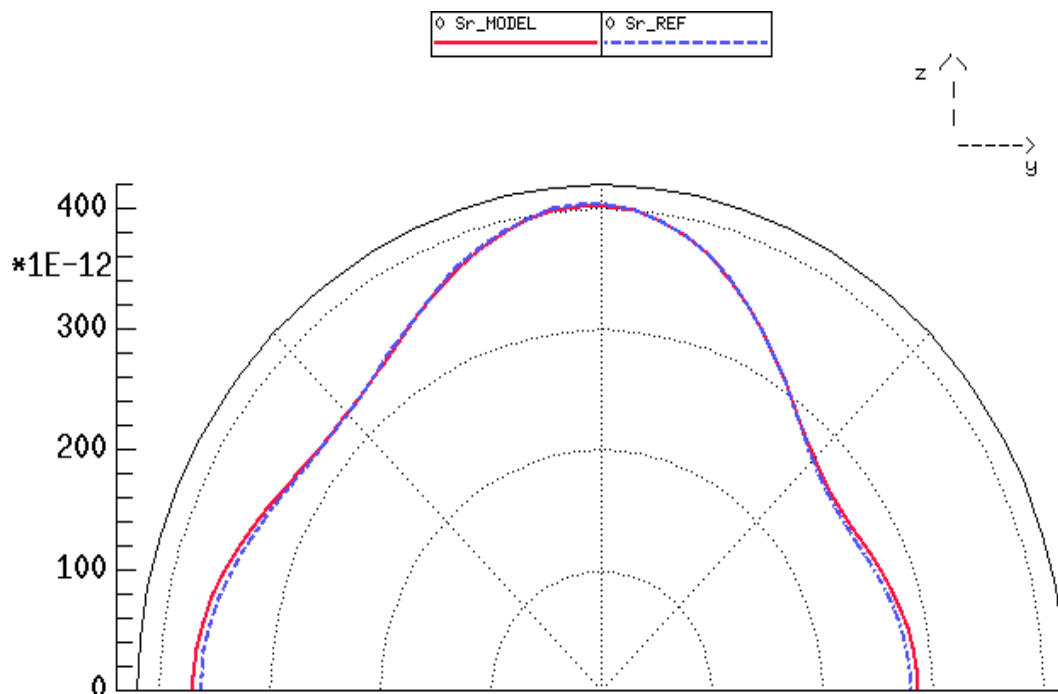


Mag. Of current on antenna
at $f = 2$ GHz

red = Model; blue = reference



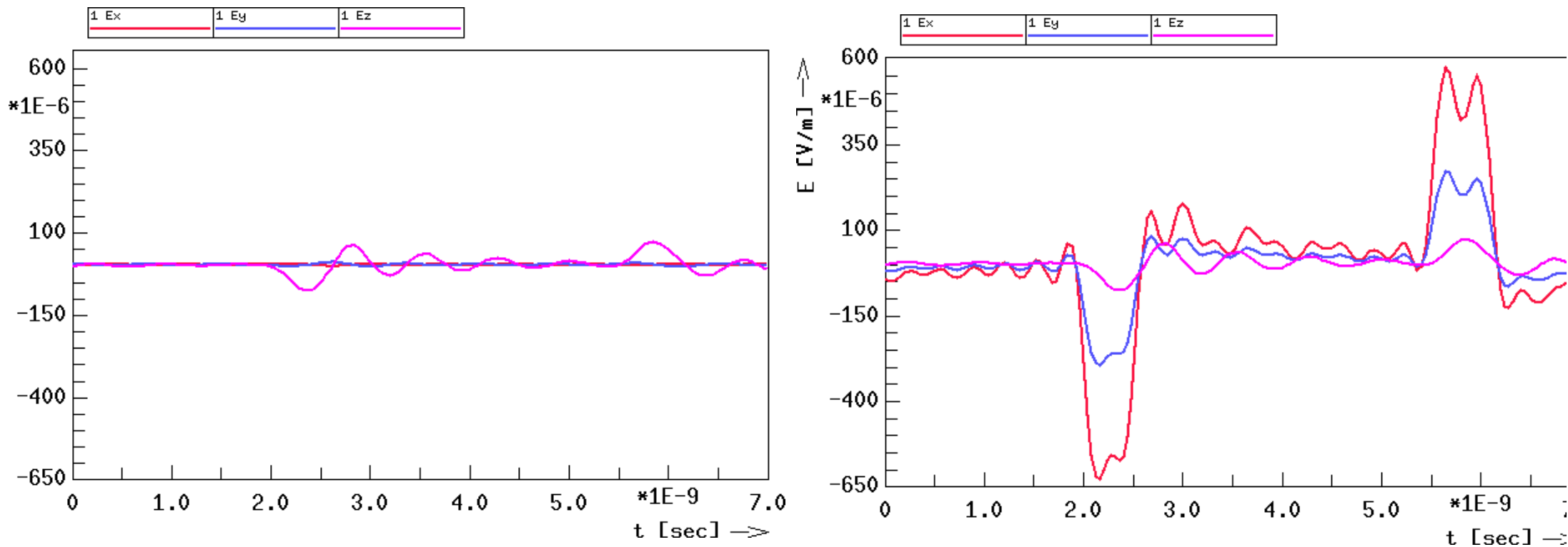
Example: Farfield-Effects



red = Model; blue = reference



Example: Comparison to Dipole Model



E-field 3m above structure; red: E_x , blue E_y , purple E_z ;
pure electric dipole model (left) and multipole model (right)



Example: Computational Effort

Computational resources:

Simulation	Calculation time	Memory used
Reference	297:43 min	95 MB
Model creation	48:12 min	21 MB
Model use	0:21 min	0.2 MB

- Efficient consideration of electromagnetic IC emission
- Enable fast analysis of different configurations
→ design optimizations



Summary

- High complexity of IC → expensive modeling necessary
⇒ *no integration in system design possible*
- Use of Multipole expansion as macro-model
⇒ *low number of necessary parameters*
- Simple integration in PCB- and system-level tools
- Good agreement with full-wave reference calculations
- Substantial gain of computational- and memory resources

